



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT FAST SWITCHING DIODE

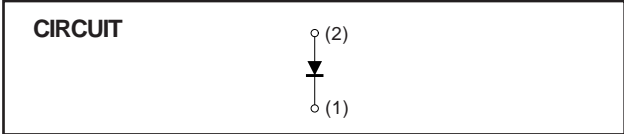
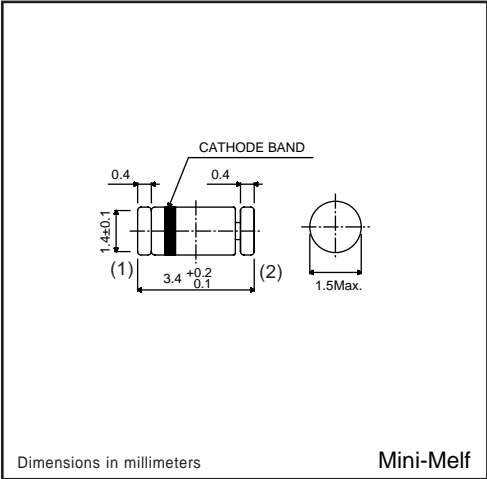
VOLTAGE 50 Volts CURRENT 200 mAmpere

LL4150GP

APPLICATION
* Extreme fast switches.

FEATURE
* Small surface mounting type. (MINI-MELF)
* High speed. ($T_{RR}=4.0nSec$ Typ.)
* Suitable for high packing density.
* Maximum total power dissipation is 500mW.

CONSTRUCTION
* Silicon epitaxial planar



MAXIMUM RATINGS (At $T_A = 25^\circ C$ unless otherwise noted)

RATINGS	SYMBOL	LL4150GP	UNITS
Peak Reverse Voltage	V_{RM}	50	Volts
Reverse Voltage	V_R	50	Volts
Repetitive Peak Forward Current	I_F	200	mAmps
Average Forward Current	I_{FAV}	200	mAmps
Peak Forward Surge Current @ $t=1.0\mu S$	I_{FSM}	0.5	Amps
Power Dissipation at $T_A=25^\circ C$	P_{tot}	500	mWatt
Maximum Capacitance (Note 1)	C_{tot}	4.0	pF
Maximum Reverse Recovery Time (Note 2)	T_{RR}	4.0	nS
Operating Temperature Range	T_J	175	$^\circ C$
Storage Temperature Range	T_{STG}	-65 to +175	$^\circ C$

ELECTRICAL CHARACTERISTICS (At $T_A = 25^\circ C$ unless otherwise noted)

CHARACTERISTICS	SYMBOL	LL4150GP	UNITS
Maximum Instantaneous Forward Voltage	V_F	1.0	Volts
Maximum Average Reverse Current at Reverse Voltage, $V_R=50V$	@ $T_A = 25^\circ C$	0.1	uAmps
	@ $T_J = 150^\circ C$	100	uAmps
Reverse Breakdown Voltage at $I_R=5mA$	V_{br}	35(min.)	Volts

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volt.
2. $I_F = -I_R = 10$ to 200mA, to 0.1 μF

RATING CHARACTERISTIC CURVES (LL4150GP)

FIG. 1 - FORWARD CHARACTERISTICS

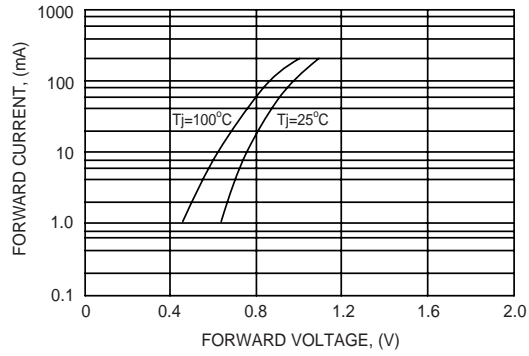


FIG. 2 - REVERSE CHARACTERISTICS

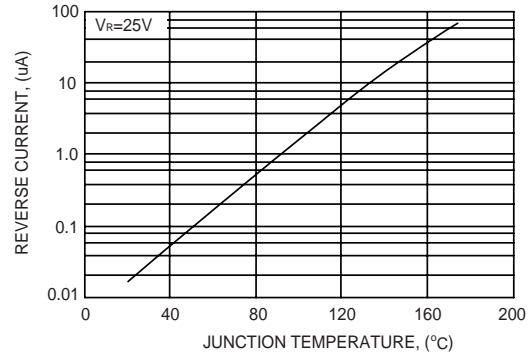


FIG. 3 - DIODE CAPACITANCE

